30V N-Channel MOSFETs

General Description

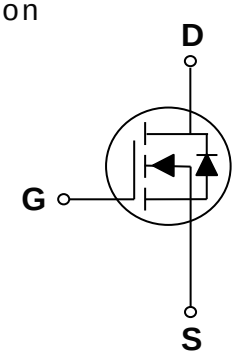
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	1.6mΩ	130A

Features

- *30V, 130A, RDS(ON) =1.6mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

PPAK5x6 Pin Configuration



Applications

- *MB / VGA / Server Vcore*
- *POL Applications*
- *SMPS 2nd SR*
- *BMS System*

Absolute Maximum Ratings **Tc=25℃ unless otherwise noted**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	130	A
	Drain Current – Continuous (T_C=100℃)	82	A
I_{DM}	Drain Current – Pulsed[1]	520	A
EAS	Single Pulse Avalanche Energy[2]	245	mJ
IAS	Single Pulse Avalanche Current[2]	70	A
P_D	Power Dissipation (T_C=25℃)	166	W
	Power Dissipation – Derate above 25℃	1.33	W/℃
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.9	℃/W

30V N-Channel MOSFETs

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Static State Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=27V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=85℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance[3]	V_{GS}=10V , I_D=30A	---	1.2	1.6	mΩ
		V_{GS}=4.5V , I_D=15A	---	1.8	2.4	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1	1.6	2.5	V
gfs	Forward Transconductance	V_{DS}=10V , I_D=15A	---	30	---	S

Dynamic Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=15V , V_{GS}=4.5V , I_D=10A	---	65	120	nC
Q_{gs}	Gate-Source Charge[3,4]		---	16	30	
Q_{gd}	Gate-Drain Charge[3,4]		---	21	40	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω I_D=1A	---	28	56	ns
T_r	Rise Time[3,4]		---	45	90	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	105	200	
T_f	Fall Time[3,4]		---	40	80	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	7720	11000	pF
C_{oss}	Output Capacitance		---	945	1400	
C_{rss}	Reverse Transfer Capacitance		---	435	650	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	1.2	2.4	Ω

Guaranteed Avalanche Energy

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	V_{DD}=25V, L=0.1mH, IAS=30A	45	---	---	mJ

Drain-Source Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	130	A
I_{SM}	Pulsed Source Current[3]		---	---	260	A
V_{SD}	Diode Forward Voltage[3]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=70A.,R_G=25Ω ,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

30V N-Channel MOSFETs

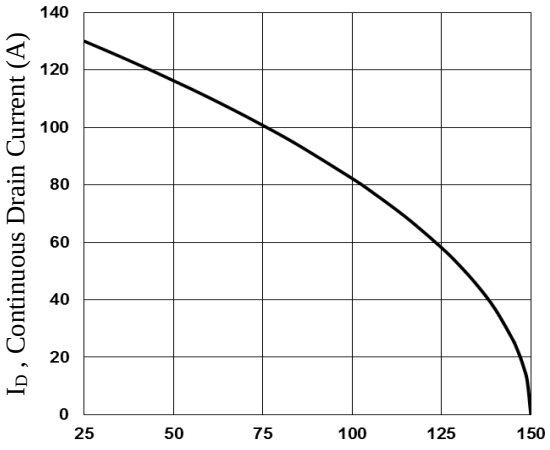


Fig.1 Continuous Drain Current vs. T_C

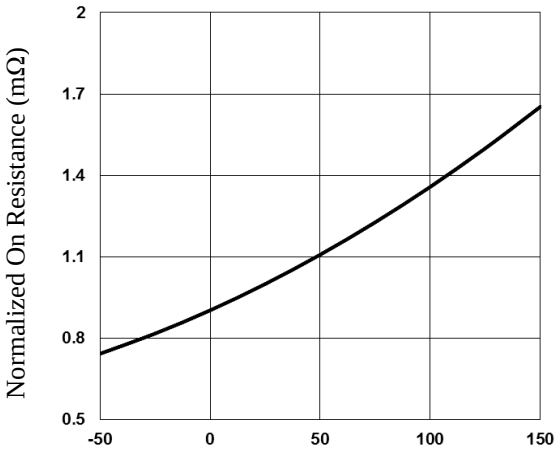


Fig.2 Normalized RDSON vs. T_J

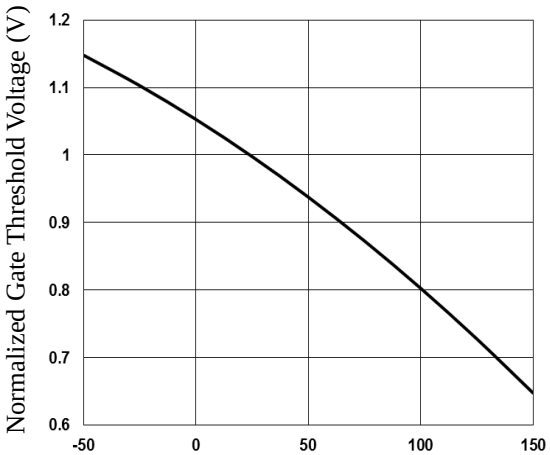


Fig.3 Normalized V_{th} vs. T_J

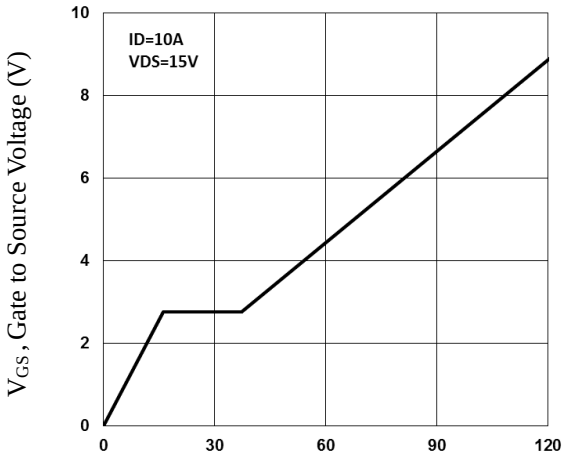


Fig.4 Gate Charge Waveform

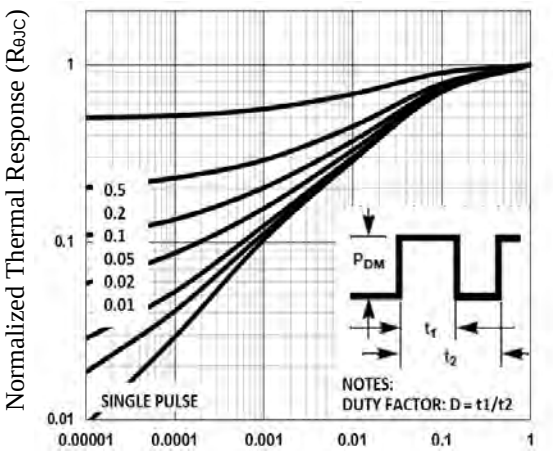


Fig.5 Normalized Transient Impedance

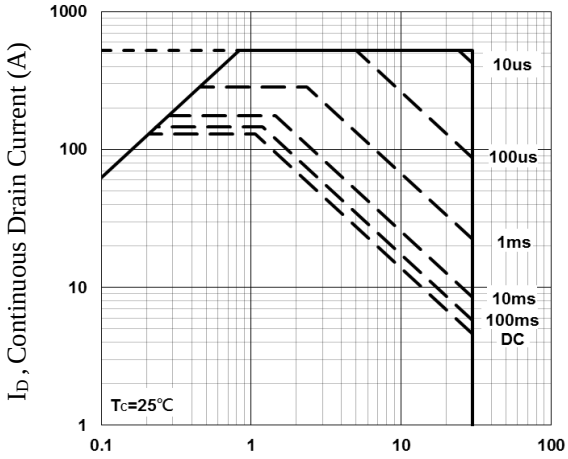


Fig.6 Maximum Safe Operation Area

30V N-Channel MOSFETs

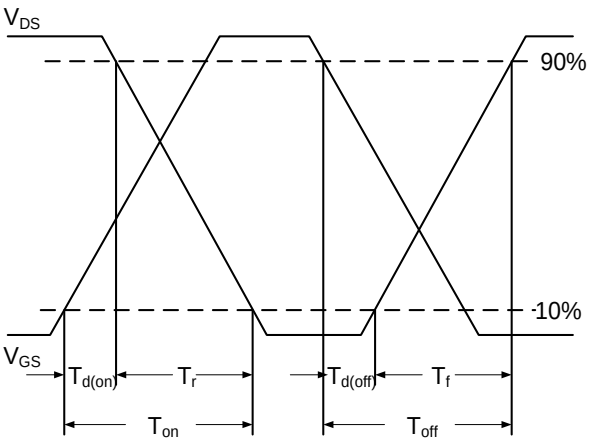


Fig.7 Switching Time Waveform

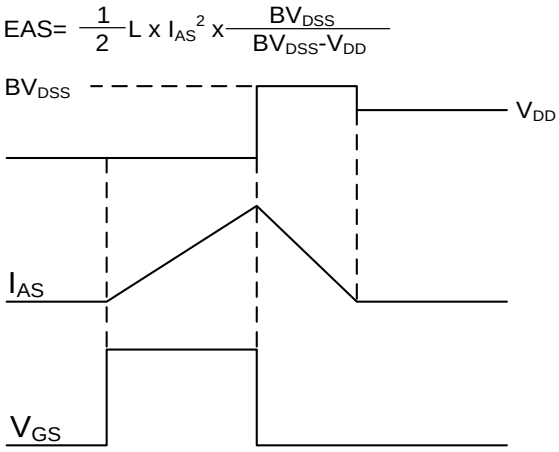
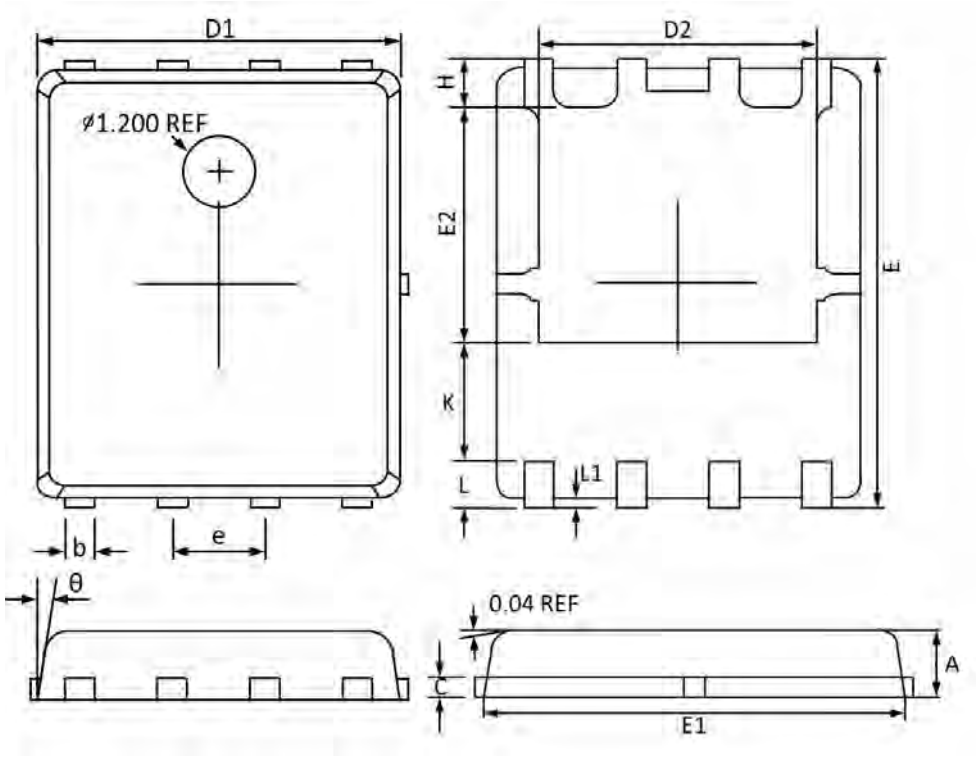


Fig.8 EAS Waveform

30V N-Channel MOSFETs

PPAK5x6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
b	0.510	0.330	0.020	0.013
C	0.300	0.200	0.012	0.008
D1	5.100	4.800	0.201	0.189
D2	4.100	3.610	0.161	0.142
E	6.200	5.900	0.244	0.232
E1	5.900	5.700	0.232	0.224
E2	3.780	3.350	0.149	0.132
e	1.27BSC		0.05BSC	
H	0.700	0.410	0.028	0.016
K	1.500	1.100	0.059	0.043
L	0.710	0.510	0.028	0.020
L1	0.200	0.060	0.008	0.002
θ	12°	0°	12°	0°